

MJD32C

Low voltage PNP power transistor

Features

- Surface-mounting TO-252 power package in tape and reel
- Complementary to the NPN type MJD31C

Application

 General purpose linear and switching equipment

Description

The device is manufactured in planar technology with "base island" layout. The resulting transistor shows exceptional high gain performance coupled with very low saturation voltage.

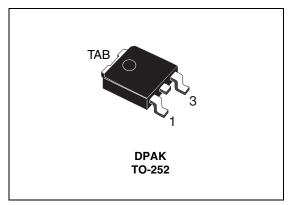
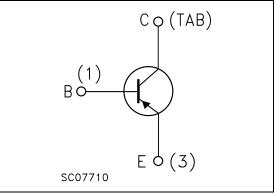


Figure 1. Internal schematic diagram



Order code	Marking	Package	Packaging
MJD32CT4	MJD32C	DPAK	Tape and reel

January 2010

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1 Electrical ratings

Table 2.	Absolute	maximum	ratings
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Symbol	Parameter	Value	Unit
V _{CBO}	Collector-base voltage (I _E = 0)	-100	V
V _{CEO}	Collector-emitter voltage $(I_B = 0)$	-100	V
V _{EBO}	Emitter-base voltage ($I_{C} = 0$)	-5	V
Ι _C	Collector current	-3	А
I _{CM}	Collector peak current	-5	А
Ι _Β	Base current	-1	А
P _{TOT}	Total dissipation at $T_c = 25 \ ^{\circ}C$	15	W
T _{STG}	Storage temperature	-65 to 150	°C
TJ	Max. operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thJC}	Thermal resistance junction-case Max	8.3	°C/W
R _{thJP} ⁽¹⁾	Thermal resistance junction-pcb Max	50	°C/W

1. When mounted on FR-4 board of 1 inch², 2 oz Cu.



2 Electrical characteristics

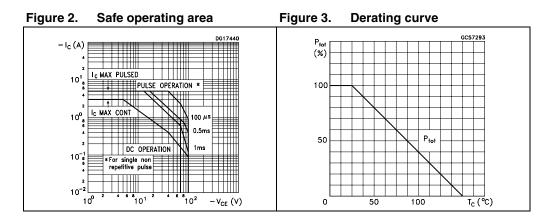
 T_{case} = 25 °C unless otherwise specified.

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector cut-off current (V _{BE} = 0)	V _{CE} = - 100 V		-	-20	μA
I _{CEO}	Collector cut-off current $(I_B = 0)$	V _{CB} = - 60 V		-	-50	μA
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = - 5 V		-	-0.1	mA
V _{CEO(sus)} ⁽¹⁾	Collector-emitter sustaining voltage (I _B = 0)	I _C = - 30 mA	-100	-		v
V _{CE(sat)} ⁽¹⁾	Collector-emitter saturation voltage	I _C = - 3 A I _B = - 375 mA		-	-1.2	v
V _{BE(on)} ⁽¹⁾	Base-emitter on voltage	$I_{C} = -3 A$ $V_{CE} = -4 V$		-	-1.8	V
h _{FE}	DC current gain		25 10	-	50	

Table 4. Electrical characteristics

1. Pulse test: pulse duration \leq 300 µs, duty cycle \leq 2 %

2.1 Electrical characteristic (curves)





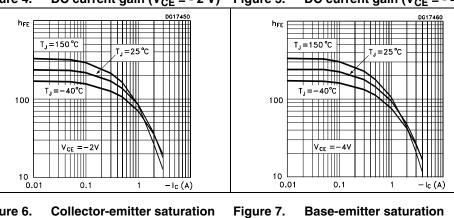
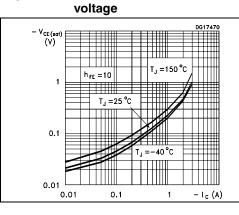


Figure 4. Figure 5. DC current gain (V_{CE} = - 4 V) DC current gain ($V_{CE} = -2 V$)

Figure 6. **Collector-emitter saturation**



voltage

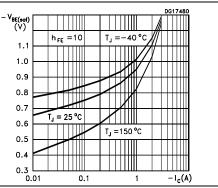
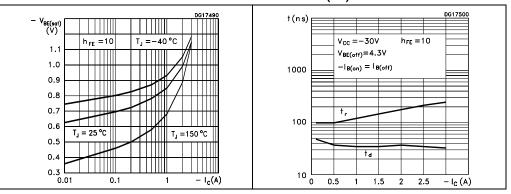


Figure 8. Base-emitter on voltage

Figure 9. **Resistive load switching time** (on)

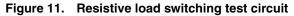


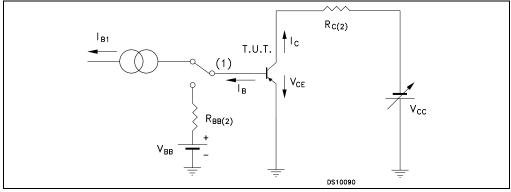


DG17510 t(ns) $V_{CC} = -30V$ $h_{FE} = 10$ V_{BE(off)}=4.3V $-I_{B(on)} = |_{B(off)}$ t, 1000 $t_{\rm f}$ 100 10 └ 0 0.5 1.5 2 2.5 - I_c (A)

Figure 10. Resistive load switching time (off)

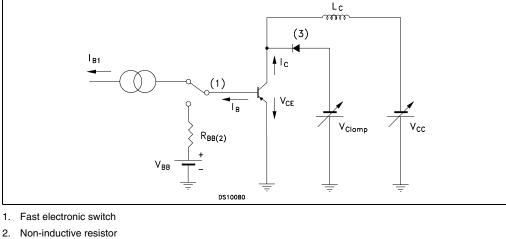
2.2 Test circuits





- 1. Fast electronic switch
- 2. Non-inductive resistor

Figure 12. Inductive load switching test circuit



3. Fast recovery rectifier



3 Package mechanical data

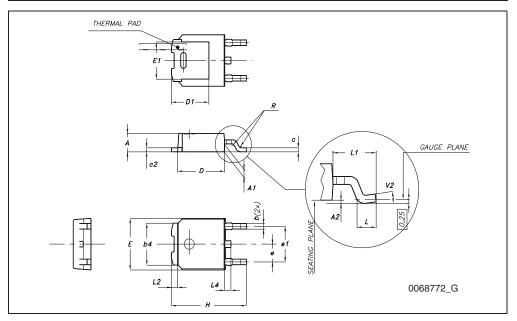
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TO-252 (DPAK) mechanical data					
DIM.		mm.			
Dilwi.	min.	typ	max.		
A	2.20		2.40		
A1	0.90		1.10		
A2	0.03		0.23		
b	0.64		0.90		
b4	5.20		5.40		
С	0.45		0.60		
c2	0.48		0.60		
D	6.00		6.20		
D1		5.10			
E	6.40		6.60		
E1		4.70			
е		2.28			
e1	4.40		4.60		
Н	9.35		10.10		
L	1				
L1		2.80			
L2		0.80			
L4	0.60		1		
R		0.20			
V2	0 °		8 °		



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4 Revision history

Table 5.Document revision history

Date	Revision	Changes
25-Jun-2007	1	Initial release.
09-Nov-2009	2	Updated package mechanical data.
14-Jan-2010	3	Modified Table 3 on page 2.

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